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Contents

vii *Conference Committee*

DTCO AND STCO I

- 12954 02 **The effect of metal gate recess profile on FinFET performance** [12954-1]
- 12954 03 **Transistor profiling for quantitative evaluation of variability in transistor characteristics due to layout dependent effects (LDEs)** [12954-2]
- 12954 04 **Study of EUV stochastic defect on wafer yield** [12954-4]
- 12954 05 **Manufacturing-friendly curvilinear standard cell design** [12954-5]
- 12954 06 **In-design DFM pattern optimization with ML models for dynamic fixing guidance selection and implementation** [12954-60]

DTCO AND STCO II

- 12954 09 **High-density standard cell libraries with backside power options in A14 nanosheet node** [12954-8]
- 12954 0A **Advanced device extraction and LVS (layout vs. schematic) with pattern matching applications** [12954-9]
- 12954 0B **Application-driven optimizations of metal stack and PDN (power delivery network) using machine learning framework** [12954-10]
- 12954 0C **A transistor sizing method for standard-cell optimization considering lithography effects** [12954-11]

3DIC, HETEROGENEOUS INTEGRATION

- 12954 0D **Advanced wafer engineering for minimizing overlay: tailoring and reducing wafer stress and distortion** [12954-12]
- 12954 0E **Investigation of die-cost scaling scenarios in future technologies** [12954-13]

MACHINE LEARNING I

- 12954 0F **An artificial intelligence machine learning (AI/ML) approach with cross-technology node learning for multi-layer process defect predictions (Invited Paper)** [12954-14]
- 12954 0G **A fast and accurate PEB simulation through recurrent neural network** [12954-15]
- 12954 0H **Synthesizing ILT MB-SRAF using machine learning** [12954-17]

COMPUTATIONAL PATTERNING I

- 12954 0I **Pre-training CNN for fast EUV lithography simulation including M3D effects** [12954-18]
- 12954 0J **Open-source differentiable lithography imaging framework** [12954-19]
- 12954 0K **A novel flow of full-chip OPC model calibration and verification by utilizing SEM image contours** [12954-20]
- 12954 0L **Improving OPC model accuracy of dry resist for low k1 EUV patterning** [12954-21]
- 12954 0M **Inverse lithography mask design of displacement Talbot lithography enabled by optimization method** [12954-22]
- 12954 0N **High accuracy OPC electromagnetic full-chip modeling for curvilinear mask OPC and ILT** [12954-23]
- 12954 0O **Cloud flight plan for post-tapeout flow jobs** [12954-24]

COMPUTATIONAL PATTERNING AND MACHINE LEARNING

- 12954 0Q **Enhancing lithography printability through deep generative models for layout re-targeting** [12954-25]
- 12954 0R **A machine learning approach towards SKILL code autocompletion** [12954-26]
- 12954 0S **Advances in full-chip three-dimensional resist modeling for low k1 EUV and DUV lithography** [12954-27]
- 12954 0T **Affordable optical proximity correction runtime for EUV curvilinear mask tape-out flow** [12954-28]

COMPUTATIONAL PATTERNING II

- 12954 0V **Full-field correction for stitched double exposure high-NA EUVL processes (Invited Paper)** [12954-29]
- 12954 0X **Source mask optimization (SMO) study for high-NA EUV lithography to achieve single patterning on random logic metal** [12954-31]
- 12954 0Y **A deep learning workflow to generate free-form masks for grayscale lithography** [12954-32]
- 12954 0Z **NIL solutions using computational lithography for semiconductor device manufacturing** [12954-33]

DFM AND DFY

- 12954 10 **Pattern-based in-design fixing for improving design for manufacturability (DFM) rule compliance** [12954-34]
- 12954 11 **A new era DFM solution for yield enhancement using machine learning (ML)** [12954-35]
- 12954 12 **Digital twin technology introduction to increase yield of processes** [12954-36]

CURVILINEAR MASK DATA FOR COMPUTATIONAL PATTERNING

- 12954 14 **Simulating use of displacement Talbot lithography for high volume AR waveguide manufacturing (Invited Paper)** [12954-38]
- 12954 16 **Why the mask world is moving to curvilinear (Invited Paper)** [12954-40]
- 12954 17 **Fast full chip curvilinear MRC for advanced manufacturing nodes** [12954-41]
- 12954 18 **Model-based OPC using the MEEF matrix III** [12954-42]

POSTER SESSION

- 12954 19 **Advanced regression OPC model setup** [12954-43]
- 12954 1A **Identification of key aberrations that affect pattern imaging in EUVL** [12954-44]
- 12954 1B **Using pattern analysis to improve process window qualification cycle time** [12954-45]

- 12954 1C **Test pattern generation by conditional generative model labeled by image parameters**
[12954-47]
- 12954 1D **Improving line edge roughness using virtual fabrication** [12954-48]
- 12954 1E **Tackling data inconsistency and runtime issues in inverse lithography technology (ILT) with comparative convergence study** [12954-202]
- 12954 1F **Prediction of etch bias using random forest model** [12954-16]

DIGITAL POSTER SESSION

- 12954 1G **A study of bitline contact process variation on DRAM performance and DVC/BVC failures using virtual fabrication** [12954-3]
- 12954 1H **Using machine learning method to improve design sampling efficiency for fab applications**
[12954-46]